

# 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



# DISCRETE SEMICONDUCTORS

# DATA SHEET

# **BT300S series**Thyristors

Product specification

September 1997



#### **Thyristors**

BT300S series

BT300M series

#### **GENERAL DESCRIPTION**

Glass passivated thyristors in a plastic envelope, suitable for surface mounting, intended for use in applications high requiring voltağe bidirectional blocking capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

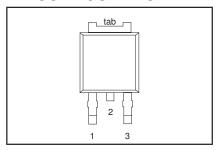
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT300S (or BT300M)- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	500R 5000 5 8 65	<b>600R</b> 600 5 8 65	800R 800 5 8 65	V A A A

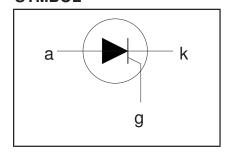
#### **PINNING - SOT428**

PIN NUMBER	Standard S	Alternative M
1	cathode	gate
2	anode	anode
3	gate	cathode
tab	anode	anode

#### **PIN CONFIGURATION**



#### **SYMBOL**



#### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V <sub>DRM</sub> , V <sub>RRM</sub>	Repetitive peak off-state voltages		-	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	<b>-800R</b> 800	V
$\begin{matrix} I_{T(AV)} \\ I_{T(RMS)} \\ I_{TSM} \end{matrix}$	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 107$ °C all conduction angles half sine wave; $T_j = 25$ °C prior to surge	-		5 8		A A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10 ms t = 8.3 ms t = 10 ms	- - -		65 71 21		A A A <sup>2</sup> s
dl <sub>T</sub> /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 10 \text{ A}; I_{G} = 50 \text{ mA};$ $dI_{G}/dt = 50 \text{ mA}/\mu s$	-		50		A/μs
$egin{array}{c} I_{GM} \ V_{GM} \ V_{RGM} \end{array}$	Peak gate current Peak gate voltage Peak reverse gate voltage		- - -		2 5 5		A V V
P <sub>GM</sub> P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Peak gate power Average gate power Storage temperature	over any 20 ms period	- - -40		5 0.5 150		W W °C
I <sub>j</sub>	Operating junction temperature		-		125		°C

September 1997 1 Rev 1.100

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

**Thyristors** 

BT300S series BT300M series

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance		-	-	2.2	K/W
R <sub>th j-a</sub>	junction to mounting base Thermal resistance junction to ambient	pcb (FR4) mounted; footprint as in Fig.14	-	75	-	K/W

#### STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mA
l I <sub>L</sub>	Latching current	$V_D^2 = 12 \text{ V}; I_{GT}^2 = 0.1 \text{ A}$	-	10	40	mA
l i <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	10	20	mA
ĺΫ́	On-state voltage	$I_{T} = 12 \text{ A}$	-	1.35	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 \text{ A}$ ; $T_i = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I <sub>D</sub> , I <sub>R</sub>	Off-state leakage current	$V_D = V_{DRM(max)}^{Station}$ ; $V_R = V_{RRM(max)}$ ; $V_i = 125  ^{\circ}C$	-	0.1	0.5	mA

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$\begin{aligned} V_{\text{DM}} &= 67\% \ V_{\text{DRM(max)}}; \ T_j = 125 \ ^{\circ}\text{C}; \\ \text{exponential waveform.} \\ &\qquad \qquad \text{Gate open circuit} \\ &\qquad \qquad R_{\text{GK}} = 100 \ \Omega \end{aligned}$	50 200	100 1000		V/μs V/μs
t <sub>gt</sub>	Gate controlled turn-on time Circuit commutated	$ \begin{aligned} &I_{TM} = 10 \text{ A; } V_D = V_{DRM(max)}; \ I_G = \widetilde{0}.1 \text{ A; } \\ &dI_G/dt = 5 \text{ A/}\mu s \\ &V_D = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}C; \\ &I_{TM} = 12 \text{ A; } V_B = 25 \text{ V; } dI_{TM}/dt = 30 \text{ A/}\mu s; \end{aligned} $	-	2 70	-	μs μs
ч	turn-off time	$I_{TM} = 12 \text{ A}; V_R = 25 \text{ V}; dI_{TM}/dt = 30 \text{ A/}\mu\text{s}; dV_D/dt = 50 \text{ V/}\mu\text{s}; R_{GK} = 100 \Omega$				·

## **Thyristors**

BT300S series BT300M series

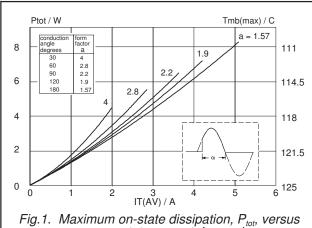


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$ .

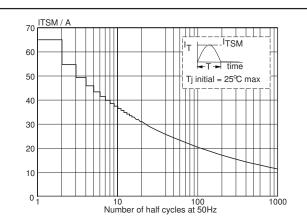


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

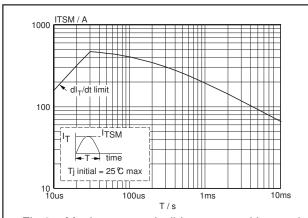


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

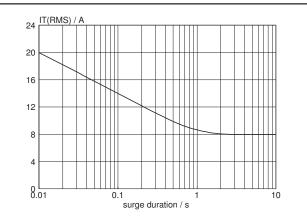


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 107 ^{\circ}\text{C}$ .

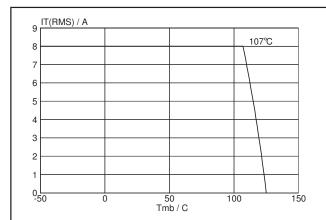
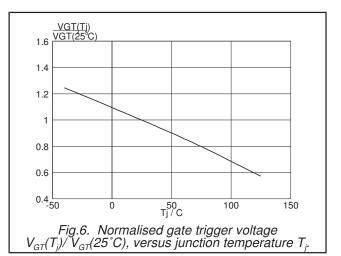
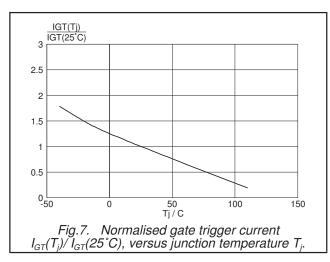


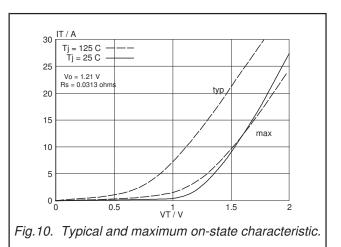
Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

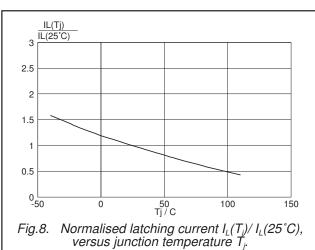


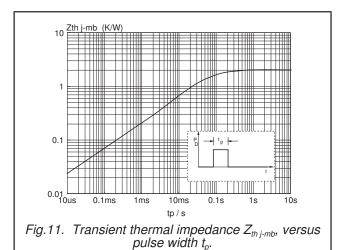
## **Thyristors**

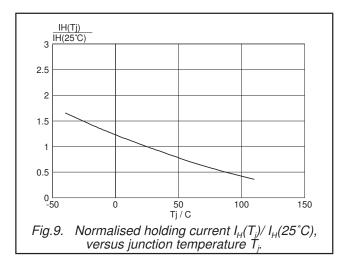
BT300S series BT300M series

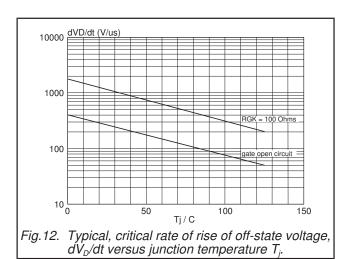








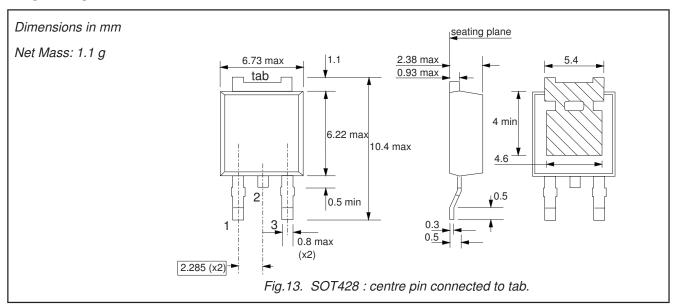




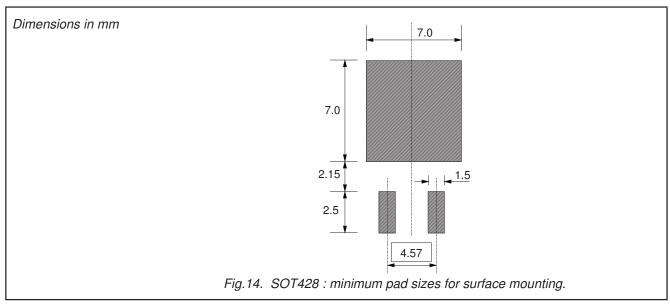
**Thyristors** 

BT300S series BT300M series

#### **MECHANICAL DATA**



#### **MOUNTING INSTRUCTIONS**



#### **Notes**

1. Plastic meets UL94 V0 at 1/8".

# Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet Production This document contains the product specification.		This document contains the product specification.

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